

1-Mbit (64K x 16) Static RAM

Features

- **Very high speed**
 - 55 ns
- **Temperature Ranges**
 - Industrial: -40°C to 85°C
 - Automotive: -40°C to 125°C
- **Wide voltage range**
 - 2.2V - 3.6V
- **Pin compatible with CY62126BV**
- **Ultra-low active power**
 - Typical active current: 0.85 mA @ f = 1 MHz
 - Typical active current: 5 mA @ f = f_{Max} (55 ns speed)
- **Ultra-low standby power**
- **Easy memory expansion with $\overline{\text{CE}}$ and $\overline{\text{OE}}$ features**
- **Automatic power-down when deselected**
- **Available in Pb-free and non Pb-free 48-ball VFBGA and 44-pin TSOP Type II packages**

Functional Description^[1]

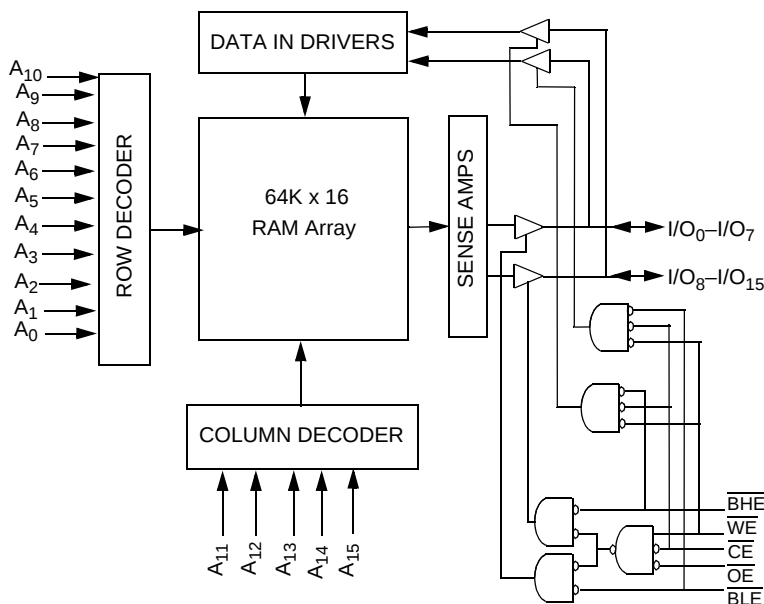
The CY62126DV30 is a high-performance CMOS static RAM organized as 64K words by 16 bits. This device features

advanced circuit design to provide ultra-low active current. This is ideal for providing More Battery Life™ (MoBL®) in portable applications such as cellular telephones. The device also has an automatic power-down feature that significantly reduces power consumption by 90% when addresses are not toggling. The device can be put into standby mode reducing power consumption by more than 99% when deselected ($\overline{\text{CE}}$ HIGH). The input/output pins (I/O₀ through I/O₁₅) are placed in a high-impedance state when: deselected ($\overline{\text{CE}}$ HIGH), outputs are disabled ($\overline{\text{OE}}$ HIGH), both Byte High Enable and Byte Low Enable are disabled ($\overline{\text{BHE}}$, $\overline{\text{BLE}}$ HIGH) or during a write operation ($\overline{\text{CE}}$ LOW and $\overline{\text{WE}}$ LOW).

Writing to the device is accomplished by taking Chip Enable ($\overline{\text{CE}}$) and Write Enable ($\overline{\text{WE}}$) inputs LOW. If Byte Low Enable ($\overline{\text{BLE}}$) is LOW, then data from I/O pins (I/O₀ through I/O₇), is written into the location specified on the address pins (A₀ through A₁₅). If Byte High Enable ($\overline{\text{BHE}}$) is LOW, then data from I/O pins (I/O₈ through I/O₁₅) is written into the location specified on the address pins (A₀ through A₁₅).

Reading from the device is accomplished by taking Chip Enable ($\overline{\text{CE}}$) and Output Enable ($\overline{\text{OE}}$) LOW while forcing the Write Enable ($\overline{\text{WE}}$) HIGH. If Byte Low Enable ($\overline{\text{BLE}}$) is LOW, then data from the memory location specified by the address pins will appear on I/O₀ to I/O₇. If Byte High Enable ($\overline{\text{BHE}}$) is LOW, then data from memory will appear on I/O₈ to I/O₁₅. See the truth table at the back of this data sheet for a complete description of read and write modes.

Logic Block Diagram



Note:

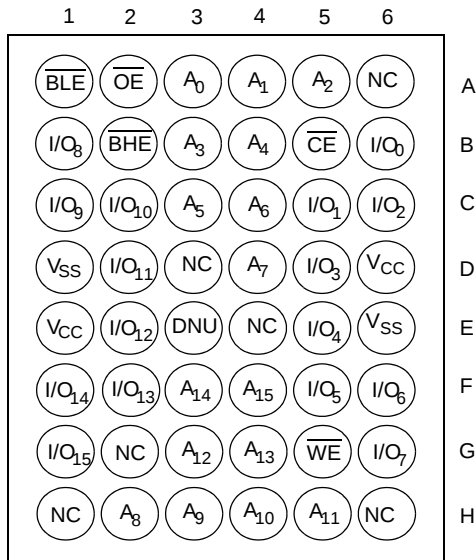
1. For best-practice recommendations, please refer to the Cypress application note "System Design Guidelines" on <http://www.cypress.com>.

Product Portfolio

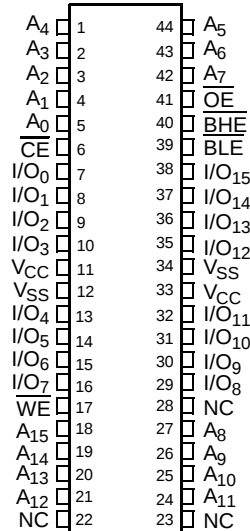
Product	Range	V _{CC} Range (V)			Speed (ns)	Power Dissipation					
						Operating, I _{CC} (mA)				Standby, I _{SB2} (μA)	
						f = 1 MHz		f = f _{Max}			
		Min.	Typ.	Max.		Typ. ^[2]	Max.	Typ. ^[2]	Max.	Typ. ^[2]	Max.
CY62126DV30L	Automotive	2.2	3.0	3.6	55	0.85	1.5	5	10	1.5	15
CY62126DV30LL	Industrial				55	0.85	1.5	5	10	1.5	4

Pin Configurations^[3, 4]

**48-ball VFBGA
Top View**



**TSOP II (Forward)
Top View**



Notes:

- Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at V_{CC} = V_{CC(typ)}, T_A = 25°C.
- NC pins are not connected to the die.
- E3 (DNU) can be left as NC or V_{SS} to ensure proper operation. (Expansion Pins on FBGA Package: E4 - 2M, D3 - 4M, H1 - 8M, G2 - 16M, H6 - 32M).

Maximum Ratings

(Above which the useful life may be impaired. For user guidelines, not tested.)

Storage Temperature -65°C to +150°C

Ambient Temperature with
Power Applied..... -55°C to +125°C

Supply Voltage to Ground
Potential -0.3 to 3.9V

DC Voltage Applied to Outputs
in High-Z State^[6] -0.3V to $V_{CC} + 0.3V$

DC Input Voltage^[6] -0.3V to $V_{CC} + 0.3V$

Output Current into Outputs (LOW)..... 20 mA

Static Discharge Voltage..... > 2001V
(per MIL-STD-883, Method 3015)

Latch-up Current > 200 mA

Operating Range

Range	Ambient Temperature (T_A)	V_{CC} ^[7]
Industrial	-40°C to +85°C	2.2V to 3.6V
Automotive	-40°C to +125°C	2.2V to 3.6V

DC Electrical Characteristics (Over the Operating Range)

Parameter	Description	Test Conditions		CY62126DV30-55			Unit
				Min.	Typ. ^[5]	Max.	
V_{OH}	Output HIGH Voltage	$2.2V \leq V_{CC} \leq 2.7V$	$I_{OH} = -0.1 \text{ mA}$	2.0			V
		$2.7V \leq V_{CC} \leq 3.6V$	$I_{OH} = -1.0 \text{ mA}$	2.4			
V_{OL}	Output LOW Voltage	$2.2V \leq V_{CC} \leq 2.7V$	$I_{OL} = 0.1 \text{ mA}$			0.4	V
		$2.7V \leq V_{CC} \leq 3.6V$	$I_{OL} = 2.1 \text{ mA}$			0.4	
V_{IH}	Input HIGH Voltage	$2.2V \leq V_{CC} \leq 2.7V$		1.8		$V_{CC} + 0.3$	V
		$2.7V \leq V_{CC} \leq 3.6V$		2.2		$V_{CC} + 0.3$	
V_{IL}	Input LOW Voltage	$2.2V \leq V_{CC} \leq 2.7V$		-0.3		0.6	V
		$2.7V \leq V_{CC} \leq 3.6V$		-0.3		0.8	
I_{IX}	Input Leakage Current	$GND \leq V_I \leq V_{CC}$	Ind'I	-1		+1	μA
			Auto	-4		+4	
I_{OZ}	Output Leakage Current	$GND \leq V_O \leq V_{CC}$, Output Disabled	Ind'I	-1		+1	μA
			Auto	-4		+4	
I_{CC}	V_{CC} Operating Supply Current	$f = f_{Max} = 1/t_{RC}$	$V_{CC} = 3.6V$, $I_{OUT} = 0 \text{ mA}$, CMOS level		5	10	mA
		$f = 1 \text{ MHz}$			0.85	1.5	
I_{SB1}	Automatic CE Power-down Current—CMOS Inputs	$\overline{CE} \geq V_{CC} - 0.2V$, $V_{IN} \geq V_{CC} - 0.2V$, $V_{IN} \leq 0.2V$, $f = f_{Max}$ (Address and Data Only), $f = 0$ ($\overline{OE}$, $\overline{WE}$, $\overline{BHE}$ and $\overline{BLE}$)	L	Ind'I	1.5	5	μA
				Auto	1.5	15	
			LL		1.5	4	
I_{SB2}	Automatic CE Power-down Current—CMOS Inputs	$\overline{CE} \geq V_{CC} - 0.2V$, $V_{IN} \geq V_{CC} - 0.2V$ or $V_{IN} \leq 0.2V$, $f = 0$, $V_{CC} = 3.6V$	L	Ind'I	1.5	5	μA
				Auto	1.5	15	
			LL		1.5	4	

Notes:

5. Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at $V_{CC} = V_{CC(typ)}$, $T_A = 25^\circ\text{C}$.

6. $V_{IL(min.)} = -2.0V$ for pulse durations less than 20 ns., $V_{IH(max.)} = V_{CC} + 0.75V$ for pulse durations less than 20 ns.

7. Full device operation requires linear ramp of V_{CC} from 0V to $V_{CC(min)}$ & V_{CC} must be stable at $V_{CC(min)}$ for 500 μs .

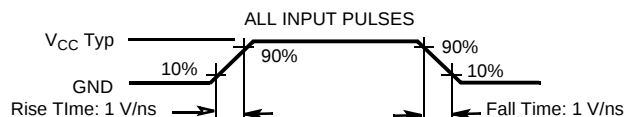
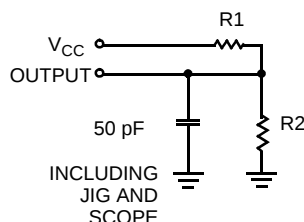
Capacitance^[8]

Parameter	Description	Test Conditions	Max.	Unit
C _{IN}	Input Capacitance	T _A = 25°C, f = 1 MHz, V _{CC} = V _{CC(typ)}	8	pF
C _{OUT}	Output Capacitance		8	pF

Thermal Resistance^[8]

Parameter	Description	Test Conditions	TSOP	VFBGA	Unit
Θ _{JA}	Thermal Resistance (Junction to Ambient)	Still Air, soldered on a 3 x 4.5 inch, 2-layer printed circuit board	55	76	°C/W
Θ _{JC}	Thermal Resistance (Junction to Case)		12	11	°C/W

AC Test Loads and Waveforms



Equivalent to: THEVENIN EQUIVALENT

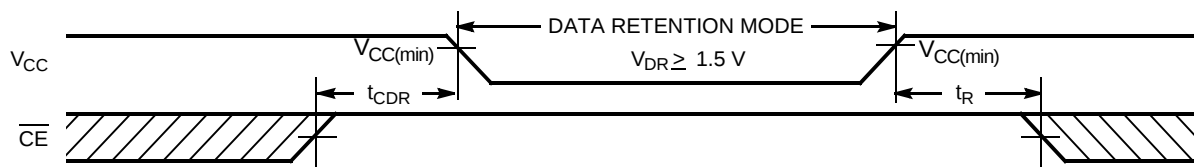
OUTPUT — R_{TH} — V_{TH}

Parameters	2.5V	3.0V	Unit
R1	16600	1103	Ohms
R2	15400	1554	Ohms
R _{TH}	8000	645	Ohms
V _{TH}	1.2	1.75	Volts

Data Retention Characteristics

Parameter	Description	Conditions	Min.	Typ ^[2]	Max.	Unit
V _{DR}	V _{CC} for Data Retention		1.5			V
I _{CCDR}	Data Retention Current	V _{CC} =1.5V, $\overline{CE} \geq V_{CC} - 0.2V$, V _{IN} ≥ V _{CC} - 0.2V or V _{IN} ≤ 0.2V				μA
		L Ind'l			4	
		L Auto			10	
		LL Ind'l			3	
t _{CDR} ^[8]	Chip Deselect to Data Retention Time		0			ns
t _R ^[9]	Operation Recovery Time		100			μs

Data Retention Waveform



Notes:

- Tested initially and after any design or process changes that may affect these parameters.
- Full device operation requires linear V_{CC} ramp from V_{DR} to V_{CC(min.)} >100 μs.

Switching Characteristics (Over the Operating Range)^[10]

Parameter	Description	CY62126DV30-55		Unit
		Min.	Max.	
Read Cycle				
t _{RC}	Read Cycle Time	55		ns
t _{AA}	Address to Data Valid		55	ns
t _{OHA}	Data Hold from Address Change	10		ns
t _{ACE}	$\overline{CE}$ LOW to Data Valid		55	ns
t _{DOE}	$\overline{OE}$ LOW to Data Valid		25	ns
t _{LZOE}	$\overline{OE}$ LOW to Low Z ^[11]	5		ns
t _{HZOE}	$\overline{OE}$ HIGH to High Z ^[11, 12]		20	ns
t _{LZCE}	$\overline{CE}$ LOW to Low Z ^[11]	10		ns
t _{HZCE}	$\overline{CE}$ HIGH to High Z ^[11, 12]		20	ns
t _{PU}	$\overline{CE}$ LOW to Power-up	0		ns
t _{PD}	$\overline{CE}$ HIGH to Power-down		55	ns
t _{DBE}	$\overline{BLE/BHE}$ LOW to Data Valid		25	ns
t _{LZBE}	$\overline{BLE/BHE}$ LOW to Low Z ^[11]	5		ns
t _{HZBE}	$\overline{BLE/BHE}$ HIGH to High-Z ^[11, 12]		20	ns
Write Cycle ^[13]				
t _{WC}	Write Cycle Time	55		ns
t _{SCE}	$\overline{CE}$ LOW to Write End	40		ns
t _{AW}	Address Set-up to Write End	40		ns
t _{HA}	Address Hold from Write End	0		ns
t _{SA}	Address Set-up to Write Start	0		ns
t _{PWE}	$\overline{WE}$ Pulse Width	40		ns
t _{BW}	$\overline{BLE/BHE}$ LOW to Write End	40		ns
t _{SD}	Data Set-up to Write End	25		ns
t _{HD}	Data Hold from Write End	0		ns
t _{HZWE}	$\overline{WE}$ LOW to High Z ^[11, 12]		20	ns
t _{LZWE}	$\overline{WE}$ HIGH to Low Z ^[11]	10		ns

Notes:

10. Test conditions assume signal transition time of 1V/ns or less, timing reference levels of $V_{CC(typ.)}/2$, input pulse levels of 0 to $V_{CC(typ.)}$, and output loading of the specified I_{OL} .

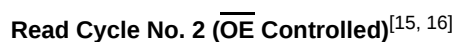
11. At any given temperature and voltage condition, t_{HZCE} is less than t_{LZCE} , t_{HZBE} is less than t_{LZBE} , t_{HZOE} is less than t_{LZOE} .

12. t_{HZOE} , t_{HZCE} , t_{HZBE} , and t_{HZWE} transitions are measured when the outputs enter a high-impedance state.

13. The internal Write time of the memory is defined by the overlap of $\overline{WE}$, $\overline{CE} = V_{IL}$, $\overline{BHE}$ and/or $\overline{BLE} = V_{IL}$. All signals must be ACTIVE to initiate a write and any of these signals can terminate a write by going INACTIVE. The data input set-up and hold timing should be referenced to the edge of the signal that terminates the write.

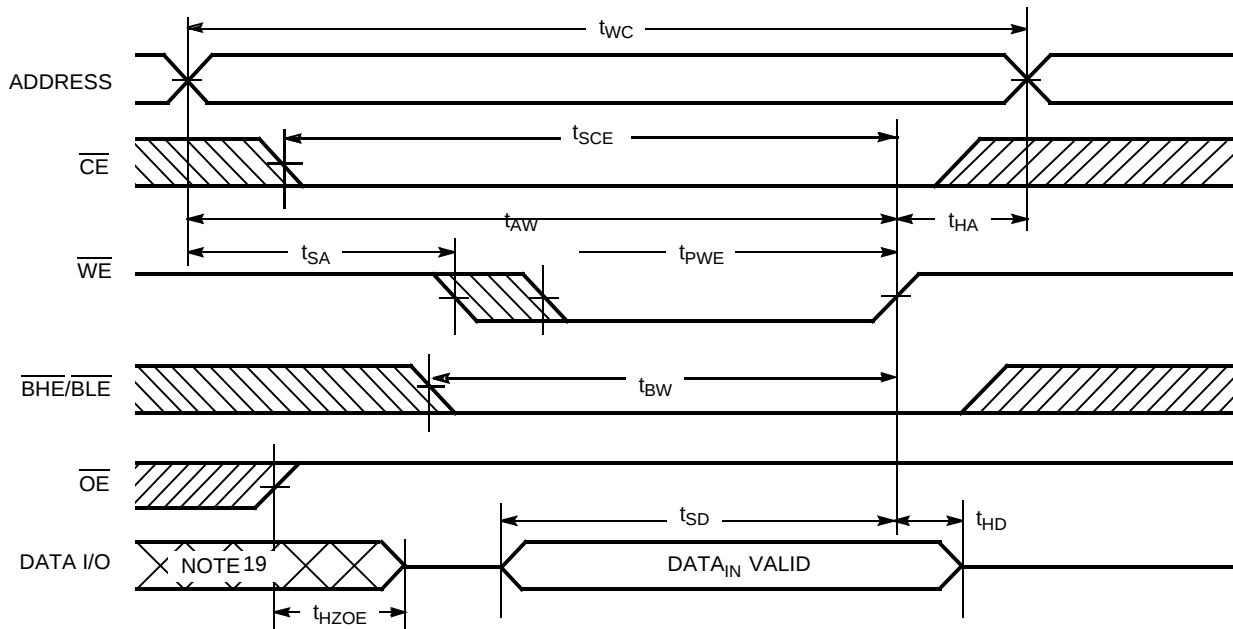


Read Cycle No. 1 (Address Transition Controlled)^[14, 15]

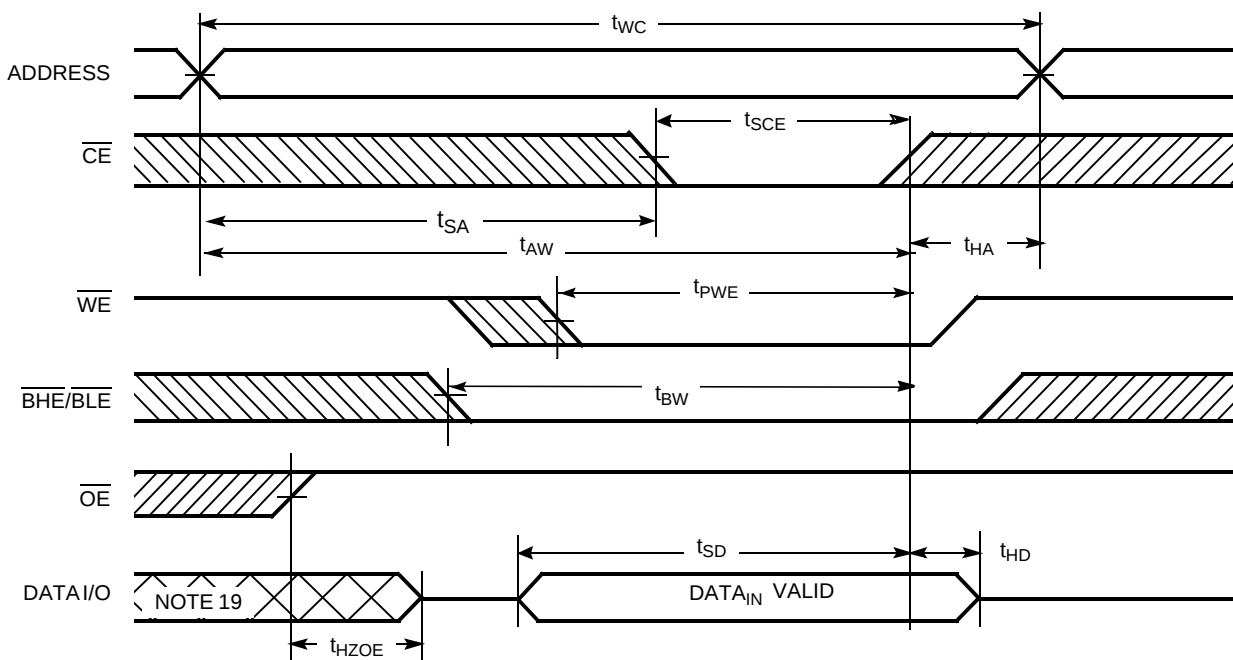


Switching Waveforms(continued)

Write Cycle No. 1 (WE Controlled)^[12, 13, 16, 17, 18]



Write Cycle No. 2 (CE Controlled)^[12, 13, 16, 17, 18]

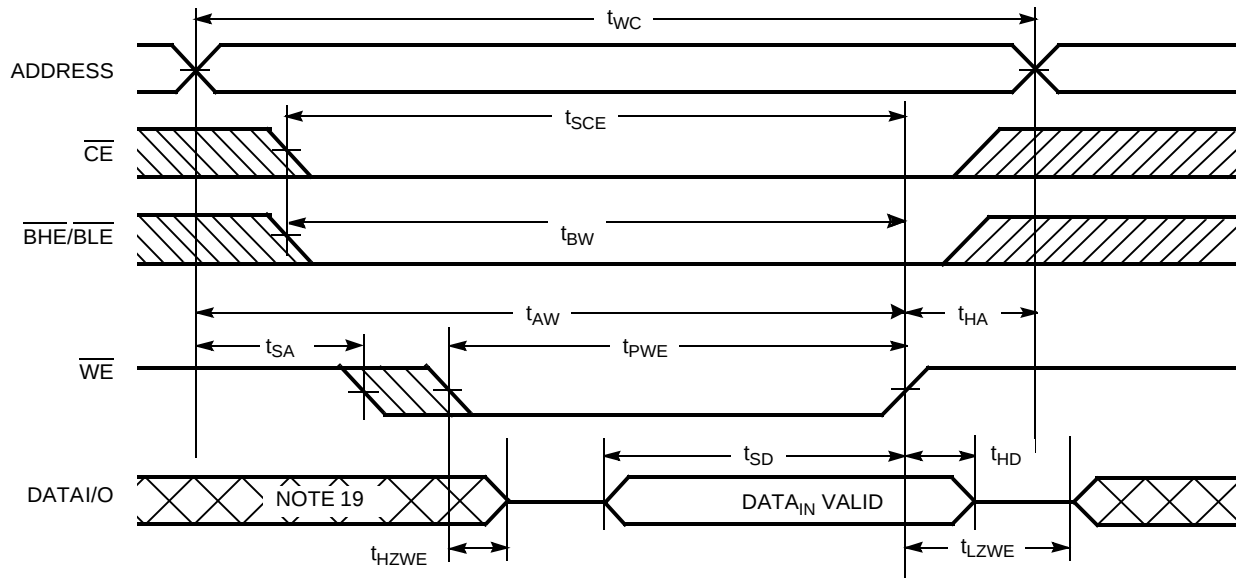


Notes:

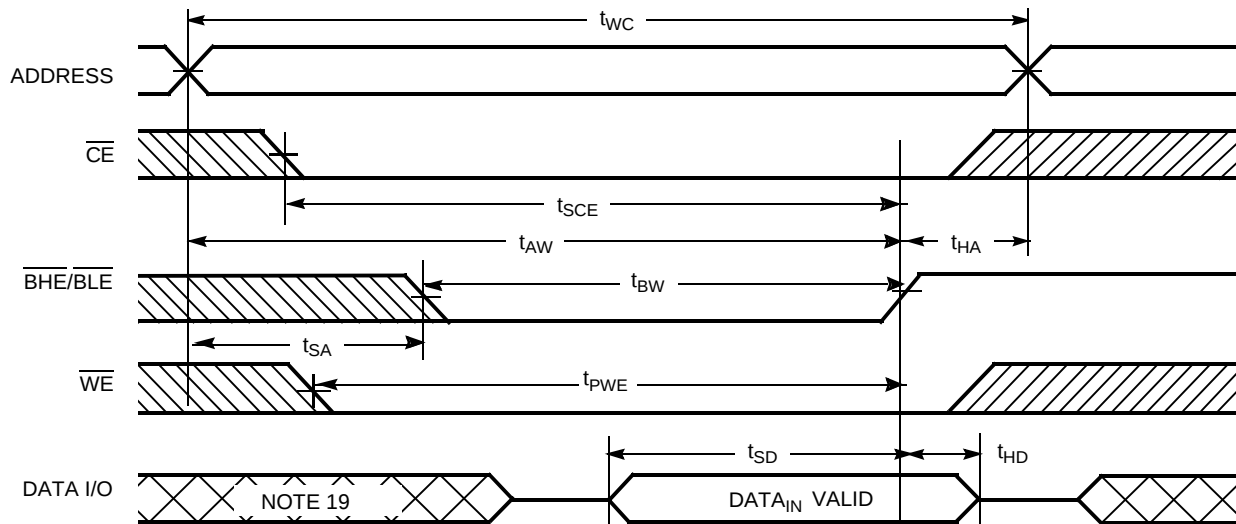
17. Data I/O is high-impedance if $\overline{OE} = V_{IH}$.
18. If $\overline{CE}$ goes HIGH simultaneously with WE HIGH, the output remains in a high-impedance state.
19. During the DON'T CARE period in the DATA I/O waveform, the I/Os are in output state and input signals should not be applied.

Switching Waveforms(continued)

Write Cycle No. 3 ($\overline{\text{WE}}$ Controlled, $\overline{\text{OE}}$ LOW)^[17, 18]



Write Cycle No. 4 ($\overline{\text{BHE/BLE}}$ -controlled, $\overline{\text{OE}}$ LOW)^[17, 18]



Truth Table

$\overline{\text{CE}}$	$\overline{\text{WE}}$	$\overline{\text{OE}}$	$\overline{\text{BHE}}$	$\overline{\text{BLE}}$	Inputs/Outputs	Mode	Power
H	X	X	X	X	High Z	Deselect/Power-Down	Standby (I_{SB})
L	X	X	H	H	High Z	Output Disabled	Active (I_{CC})
L	H	L	L	L	Data Out (I/O_0 – I/O_{15})	Read	Active (I_{CC})
L	H	L	H	L	High Z (I/O_8 – I/O_{15}); Data Out (I/O_0 – I/O_7)	Read	Active (I_{CC})
L	H	L	L	H	Data Out (I/O_8 – I/O_{15}); High Z (I/O_0 – I/O_7)	Read	Active (I_{CC})
L	L	X	L	L	Data In (I/O_0 – I/O_{15})	Write	Active (I_{CC})
L	L	X	H	L	High Z (I/O_8 – I/O_{15}); Data In (I/O_0 – I/O_7)	Write	Active (I_{CC})
L	L	X	L	H	Data in (I/O_8 – I/O_{15}); High Z (I/O_0 – I/O_7)	Write	Active (I_{CC})
L	H	H	L	L	High Z	Output Disabled	Active (I_{CC})
L	H	H	H	L	High Z	Output Disabled	Active (I_{CC})
L	H	H	L	H	High Z	Output Disabled	Active (I_{CC})

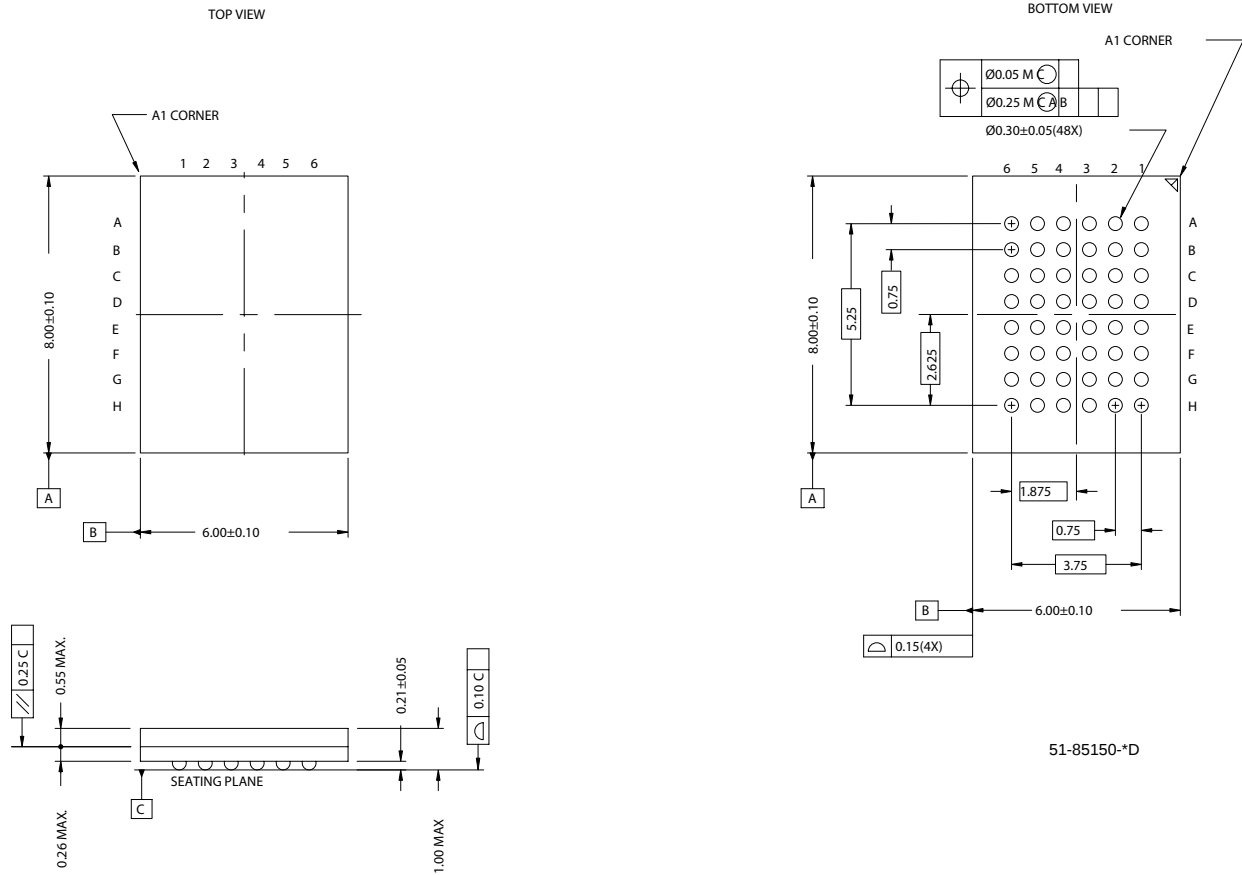
Ordering Information

Speed (ns)	Ordering Code	Package Diagram	Package Type	Operating Range
55	CY62126DV30LL-55BVI	51-85150	48-ball Fine-Pitch Ball Grid Array (6 x 8 x 1 mm)	Industrial
	CY62126DV30LL-55BVXI		48-ball Fine-Pitch Ball Grid Array (6 x 8 x 1 mm) (Pb-free)	
	CY62126DV30LL-55ZI	51-85087	44-pin TSOP II	
	CY62126DV30LL-55ZXI		44-pin TSOP II (Pb-free)	
	CY62126DV30L-55BVXE	51-85150	48-ball Fine-Pitch Ball Grid Array (6 x 8 x 1 mm) (Pb-free)	Automotive
	CY62126DV30L-55ZSXE	51-85087	44-pin TSOP II (Pb-free)	

Please contact your local Cypress sales representative for availability of these parts

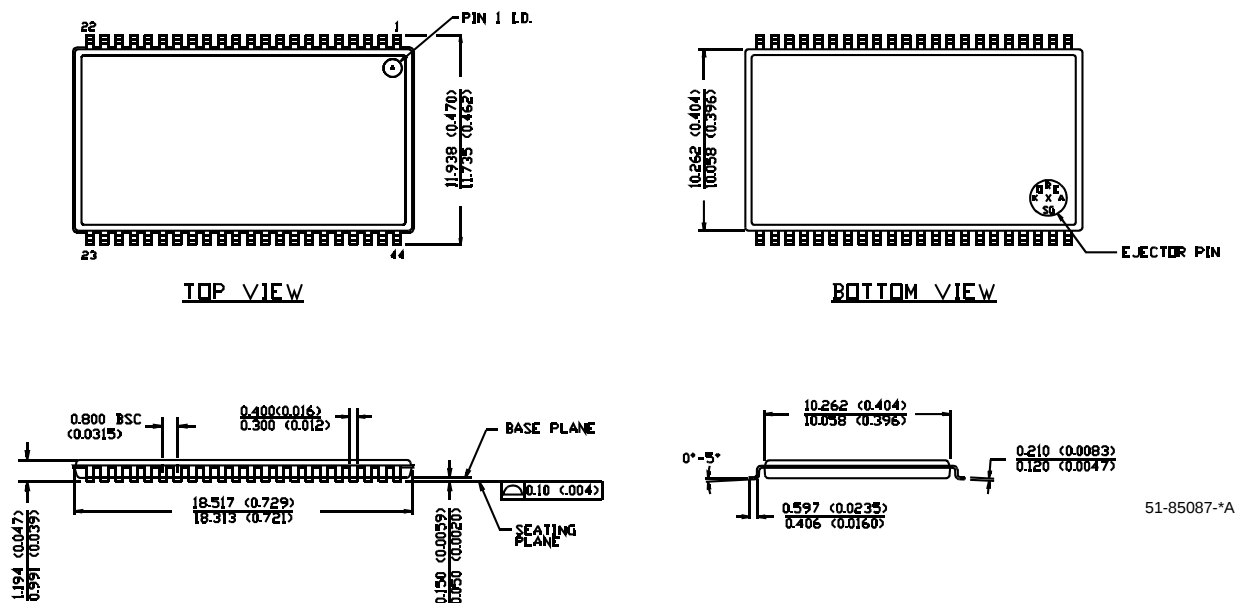
Package Diagrams

48-ball VFBGA (6 x 8 x 1 mm) (51-85150)



Package Diagrams(continued)

44-pin TSOP II (51-85087)



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Document History Page

Document Title: CY62126DV30 MoBL® 1-Mbit (64K x 16) Static RAM Document Number: 38-05230				
REV.	ECN NO.	Issue Date	Orig. of Change	Description of Change
**	117689	08/27/02	JUI	New Data Sheet
*A	127313	06/13/03	MPR	Changed From Advanced Status to Preliminary. Changed I _{SB2} to 5 μ A (L), 4 μ A (LL) Changed I _{CCDR} to 4 μ A (L), 3 μ A (LL) Changed C _{IN} from 6 pF to 8 pF
*B	128340	07/22/03	JUI	Changed from Preliminary to Final Add 70-ns speed, updated ordering information
*C	129002	08/29/03	CDY	Changed I _{CC} 1 MHz typ from 0.5 mA to 0.85 mA
*D	238050	See ECN	AJU	Fixed typo: Changed t _{DBE} from 70 ns to 35 ns
*E	316039	See ECN	PCI	Added 45-ns Speed Bin in AC, DC and Ordering Information tables Added Footnote #8 on page #4 Added Pb-free package ordering information on page # 9 Changed 44-pin TSOP-II package name from Z44 to ZS44
*F	335861	See ECN	SYT	Added Temperature Ranges in the Features Section on Page # 1 Added Automotive Product Information for CY62126DV30-L for 55 ns Added I _{SB1} and I _{SB2} values for Automotive range of CY62126DV30-L for 55 ns Added Automotive Information for I _{CCDR} in the Data Retention Characteristics table Added Pb-free packages in the ordering information Changed 44-pin TSOP-II package name from ZS44 to Z44
*G	357256	See ECN	PCI	Added Pin Configuration and Package Diagram for 56-Lead QFN Package Updated Thermal Characteristics and Ordering Information Table Added Automotive Specs for I _{IX} and I _{OZ} in the DC Electrical Characteristics table on Page# 4
*H	486789	See ECN	VKN	Changed the address of Cypress Semiconductor Corporation on Page #1 from "3901 North First Street" to "198 Champion Court" Removed 45 ns and 70ns Speed bin from Product offering Removed 56-pin QFN package Updated Ordering Information Table